

HC181 @D UghjW9 bWUdgi `UHY`HfUbg]ghc fg`

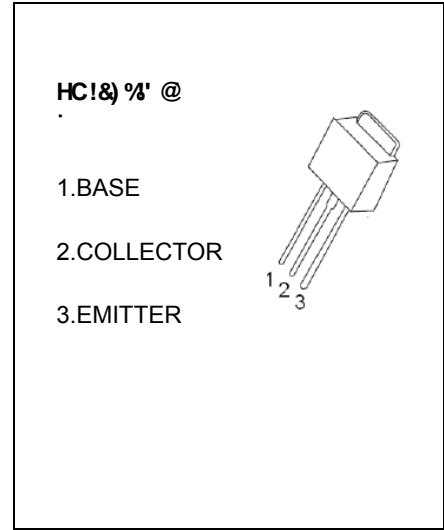
'75+) TRANSISTOR (PNP)

: 95HI F9G`

- Power Dissipation

A5L AI A`F5HB; G`fHu1&) °C`i b`Ygg`cH Yfk JgY`bcHXYL`

Gna Vc`	DUFUa YHYf`	JU i Y`	I b]h`
J76C`	Collector-Base Voltage	-40	V
J79C`	Collector-Emitter Voltage	-30	V
J96C`	Emitter-Base Voltage	-5	V
7`	Collector Current -Continuous	-2	A
D7`	Collector power dissipation	1.2	W
H`	Junction Temperature	150	°C
H _{gft} `	Storage Temperature	-55-150	°C



9 @7 HF 75 @ `7 < 5 F5 7 H9F -GH7 G`fHu1&) °C`i b`Ygg`cH Yfk JgY`gdYWZ]YXL`

DUFUa YHYf`	Gna Vc`	HYgh` WcbX]Hcbg`	A]b`	Hmf`	AU`	I b]h`
7c`YWfcf!VUgYVfYU_Xck b`j c`HU] Y`	V _{(BR)CBO}	I _C = -100μA, I _E = 0	-40			V
7c`YWfcf!Ya]HYf`VfYU_Xck b`j c`HU] Y`	V _{(BR)CEO}	I _C = -10mA, I _B = 0	-30			V
9a]HYf!VUgYVfYU_Xck b`j c`HU] Y`	V _{(BR)EBO}	I _E = -1mA, I _C = 0	-5			V
7c`YWfcf`W HcZZW ffYbhi`	I _{CBO}	V _{CB} = -40V, I _E = 0			-0.1	μA
9a]HYf`W HcZZW ffYbhi`	I _{EBO}	V _{EB} = -5V, I _C = 0			-0.1	μA
87`W ffYbhi] U]b`	h _{FE}	V _{CE} = -2V, I _C = -500mA	100		400	
7c`YWfcf!Ya]HYf`gUhi fU]cb`j c`HU] Y`	V _{CE(sat)}	I _C = -2A, I _B = -200mA			-0.8	V
	V _{CE(sat)}	I _C = -1.5A, I _B = -30mA			-2	V
HfUbg]Hcb`Z`Yei YbWni	f _T	V _{CE} = -5V, I _C = -500mA		120		MHz
7c`YWfcf`ci hdi hWUdUW]Ubw`	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		13		pF

7 @GG 75HCB`C` \ `9`

FUb`	O	Y	G
FUb] Y`	100-200	160-320	200-400